

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
13 October 2005 (13.10.2005)

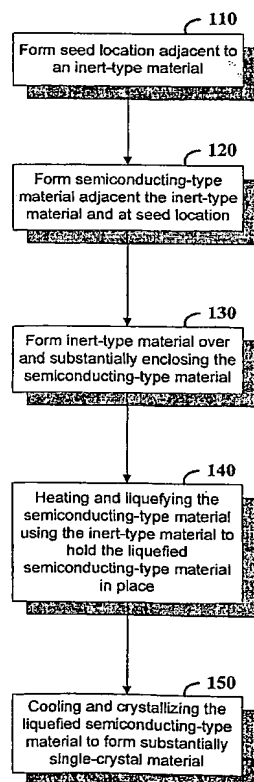
PCT

(10) International Publication Number
WO 2005/094254 A2

- (51) International Patent Classification: **Not classified**
- (21) International Application Number:
PCT/US2004/008141
- (22) International Filing Date: 17 March 2004 (17.03.2004)
- (25) Filing Language: English
- (26) Publication Language: English
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR,

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(54) Title: CRYSTALLINE-TYPE DEVICE AND APPROACH THEREFOR



(57) Abstract: Single-crystalline growth is realized using a liquid-phase crystallization approach involving the inhibition of defects typically associated with liquid-phase crystalline growth of lattice mismatched materials. According to one example embodiment, a semiconductor device structure includes a substantially single-crystal region. A liquid phase material is crystallized to form the single-crystal region using an approach involving defect inhibition for the promotion of single-crystalline growth. In some instances, this defect inhibition involves the reduction and/or elimination of defects using a relatively small physical opening via which a crystalline growth front propagates. In other instances, this defect inhibition involves causing a change in crystallization front direction relative to a crystallization seed location. The relatively small physical opening and/or the change in crystalline front direction may be implemented, for example, using a material that is relatively unreactive with the liquid-phase material to contain the crystalline growth.